

50 V; 3 A NPN low VCEsat transistor 1 January 2023

**Product data sheet** 

### 1. General description

NPN low V<sub>CEsat</sub> transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5350T

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub> and corresponding low R<sub>CEsat</sub>
- High collector current capability •
- High collector current gain
- Improved efficiency due to reduced heat generation

### 3. Applications

- Power management applications
- · Low and medium power DC/DC converters
- Supply line switching •
- Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

### 4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
I <sub>C</sub>	collector current			-	-	2	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-	5	А
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 2 A; $I_B$ = 200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C		-	100	130	mΩ

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### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		Ŭ
3	С	collector		B-K
			1 🛄 2 SOT23	sym123

### 6. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4350T	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	<u>SOT23</u>		

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS4350T	ZC%

[1] % = placeholder for manufacturing site code

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
I <sub>C</sub>	collector current			-	2	А
I <sub>CRM</sub>	repetitive peak collector current	δ ≤ 0.25; t <sub>p</sub> ≤ 100 ms		-	3	A
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	5	А
I <sub>B</sub>	base current			-	0.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[1] [4]	-	1.2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [3]

[4] Operated under pulsed conditions:  $t_p \le 100 \text{ ms}; \delta \le 0.25$ .

**Product data sheet** 

### 9. Thermal characteristics

#### Table 6. Thermal characteristics

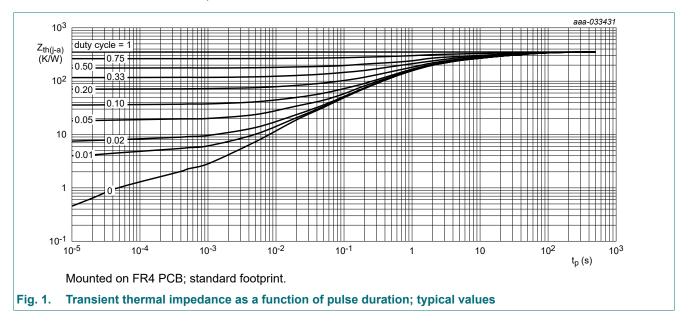
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W	
	junction to ambient		[2]	-	-	260	K/W
	[	[3]	-	-	230	K/W	
			[1] [4]	-	-	104	K/W

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[1] [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. [3]

Operated under pulsed conditions:  $t_p \le 100$  ms;  $\delta \le 0.25$ . [4]

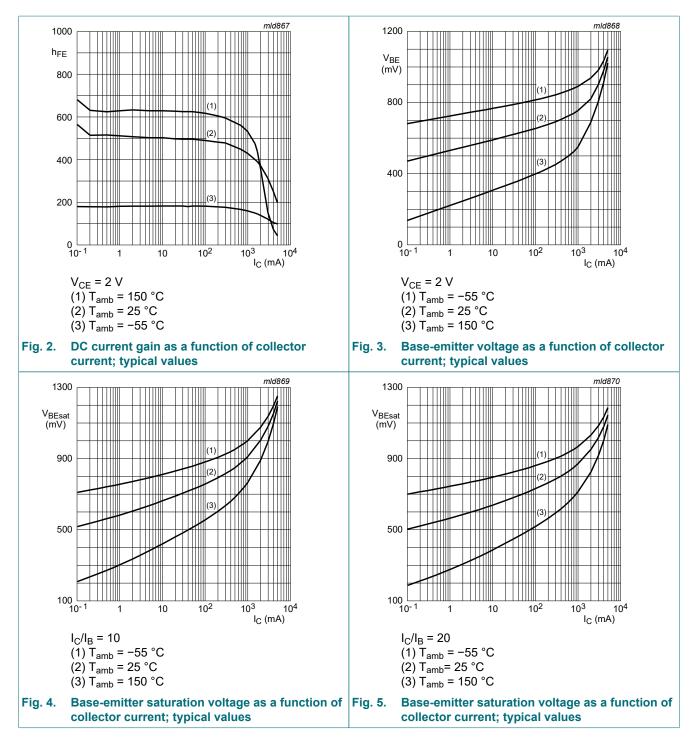


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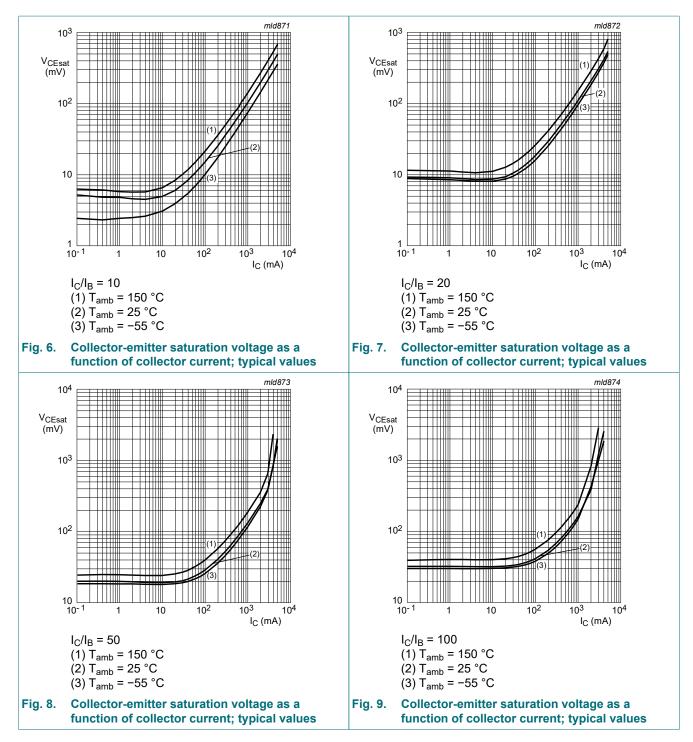
### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_{C}$ = 100 µA; $I_{E}$ = 0 A; $T_{amb}$ = 25 °C	50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	$I_C$ = 10 mA; $I_B$ = 0 A; pulsed; $t_p \le 300$ μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	I <sub>E</sub> = 100 μA; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	5	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	300	-	-	
		V <sub>CE</sub> = 2 V; I <sub>C</sub> = 500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	300	-	-	
		$V_{CE}$ = 2 V; I <sub>C</sub> = 1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	300	-	-	
		$V_{CE}$ = 2 V; I <sub>C</sub> = 2 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	200	-	-	
		$V_{CE}$ = 2 V; I <sub>C</sub> = 3 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	100	-	-	
V <sub>CEsat</sub>	collector-emitter	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	-	80	mV
	saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; T <sub>amb</sub> = 25 °C	-	-	160	mV
		I <sub>C</sub> = 2 A; I <sub>B</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	280	mV
		I <sub>C</sub> = 2 A; I <sub>B</sub> = 200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	260	mV
		I <sub>C</sub> = 3 A; I <sub>B</sub> = 300 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	370	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = 2 A; $I_B$ = 200 mA; pulsed; $t_p$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	100	130	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 2 A; I <sub>B</sub> = 100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	1.1	V
		I <sub>C</sub> = 3 A; I <sub>B</sub> = 300 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = 2 V; I <sub>C</sub> = 1 A; pulsed; t <sub>p</sub> ≤ 300 µs; $\delta$ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	1.2	V
f <sub>T</sub>	transition frequency	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	25	pF

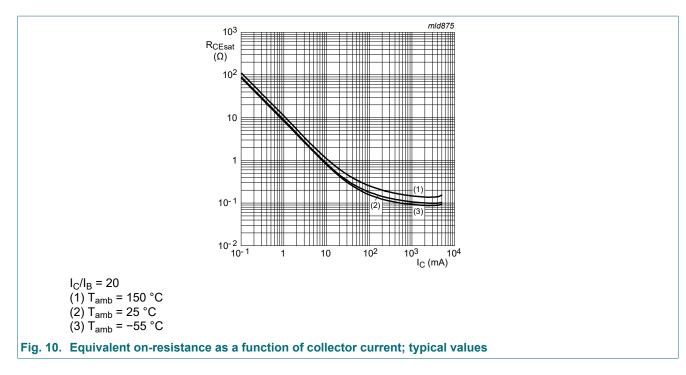
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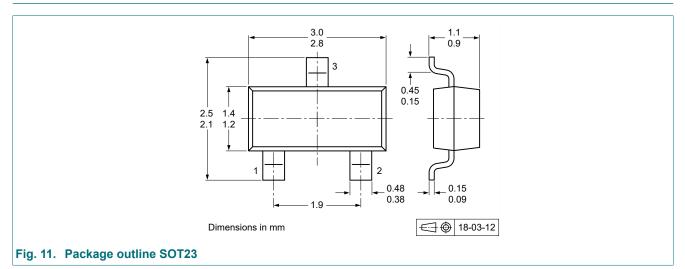


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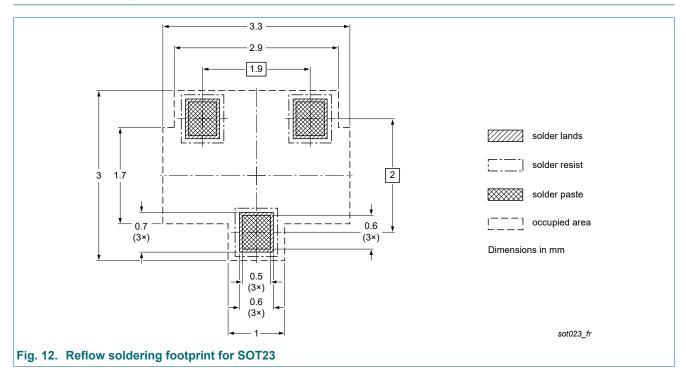


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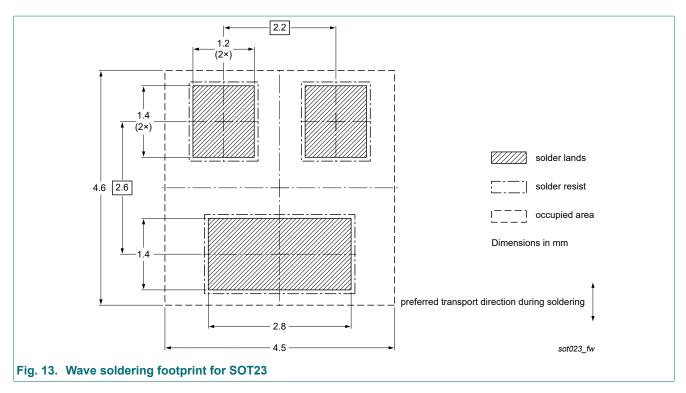
### 11. Package outline



### 12. Soldering



#### 50 V; 3 A NPN low VCEsat transistor



### **13. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS4350T v.4	20230101	Product data sheet	-	PBSS4350T v.3		
Modifications:		<ul> <li>Product changed to non-automotive qualification. Please refer to nexperia.com for automotive(-Q) product alternative(s).</li> </ul>				
PBSS4350T v.3	20220510	Product data sheet	-	PBSS4350T v.2		
PBSS4350T v.2	20040109	Product data sheet	-	PBSS4350T v.1		
PBSS4350T v.1	20020808	Product data sheet				

### 14. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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